

Abstract

5 METHOD OF FABRICATING AN INTEGRATED SILICON GERMANIUM
HETEROBIPOLAR TRANSISTOR AND AN INTEGRATED SILICON
GERMANIUM HETEROBIPOLAR TRANSISTOR

10 In a method of fabricating an integrated silicon-germanium heterobipolar transistor a silicon dioxide layer arranged between a silicon-germanium base layer and a silicon emitter layer is formed by means of Rapid Thermal Processing (RTP) to ensure enhanced component properties of the integrated silicon-germanium heterobipolar transistor.